

## Absolute Maximum Ratings, Pre-Biased NPN Transistor, Q1 (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	Vcc	50	V
Input Voltage	V <sub>IN</sub>	-10 to +40	V
Output Current	lo	30	mA
Collector Current	lc	100	mA

### Absolute Maximum Ratings, Pre-Biased PNP Transistor, Q<sub>2</sub> (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	-50	V
Input Voltage	V <sub>IN</sub>	-40 to +6	V
Output Current	lo	-100	mA
Collector Current	Ι <sub>C</sub>	-100	mA

### Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	PD	290	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{ ext{ heta}JA}$	430	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 6. For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

## Electrical Characteristics, Pre-Biased NPN Transistor, Q<sub>1</sub> (@T<sub>A</sub> = +25°C unless otherwise specified.)

Chara	cteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Valtage	(Note 7)	VI(OFF)	0.5	_	_	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100μA
Input Voltage	(Note 8)	V <sub>I(ON)</sub>		_	3	V	$V_0 = 0.3V, I_0 = 2mA$
Output Voltage		V <sub>O(ON)</sub>		0.1	0.3	V	$I_0 / I_1 = 10 \text{mA} / 0.5 \text{ mA}$
Input Current		lı –	—	_	0.18	mA	$V_1 = 5V$
Output Current		IO(OFF)		_	0.5	μΑ	$V_{CC} = 50V, V_{I} = 0V$
DC Current Gain		GI	68	_	_	_	$V_0 = 5V, I_0 = 5mA$
Gain-Bandwidth Product	(Note 9)	fT		250		MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz
Input Resistance		R <sub>1</sub>	32.9	47	61.1	kΩ	—
Resistance Ratio		R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2		

Notes: 7. The device is guaranteed to be in "OFF" state with  $V_{I(OFF)}$  up to 0.5V.

8. The device is guaranteed to be in "ON" state with  $V_{I(ON)}$  starting from 3V.

9. Characteristic of Transistor - for reference only.

### Electrical Characteristics, Pre-Biased PNP Transistor, Q2 (@TA = +25°C unless otherwise specified.)

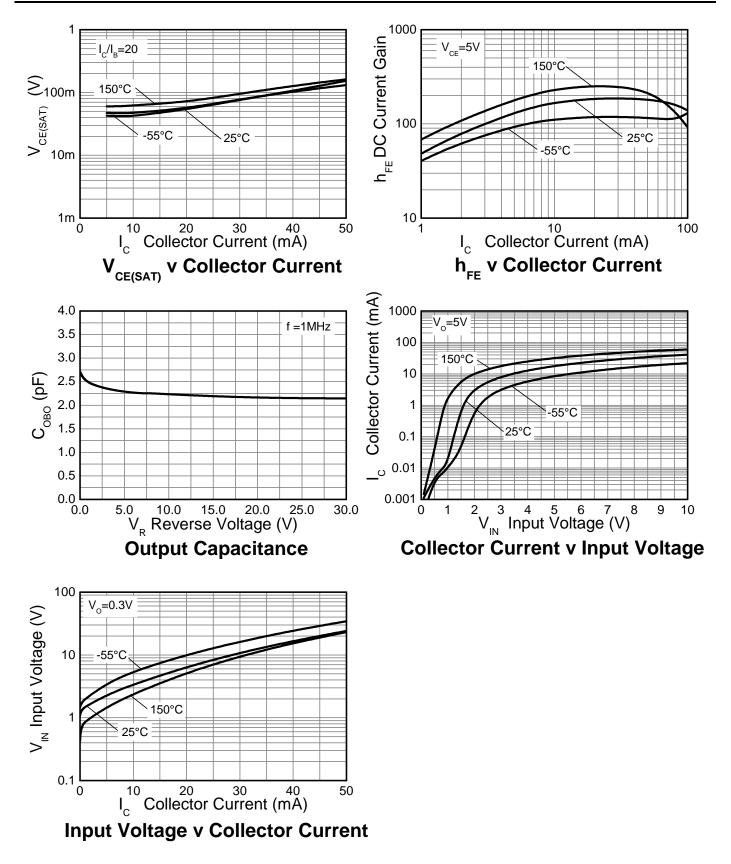
Chara	acteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	(Note 10)	VI(OFF)	-0.3	_	_	V	$V_{CC} = -5V, I_{O} = -100 \mu A$
input voltage	(Note 11)	V <sub>I(ON)</sub>	_	_	-1.4	V	V <sub>O</sub> = -0.3V, I <sub>O</sub> = -1mA
Output Voltage		V <sub>O(ON)</sub>	_	-0.1	-0.3	V	I <sub>O</sub> / I <sub>I</sub> = -5mA/-0.25 mA
Input Current		lı –	—	_	-0.88	mA	$V_{I} = -5V$
Output Current		I <sub>O(OFF)</sub>	_	_	-0.5	μA	$V_{CC} = -50V, V_{I} = 0V$
DC Current Gain		GI	68	_	—	_	$V_0 = -5V, I_0 = -5mA$
Gain-Bandwidth Product	(Note 9)	f⊤	_	250	_	MHz	$V_{CE} = -10V, I_E = 5mA, f = 100MHz$
Input Resistance		R <sub>1</sub>	7	10	13	kΩ	—
Resistance Ratio		R <sub>2</sub> /R <sub>1</sub>	3.7	4.7	5.7	_	

Notes: 10. The device is guaranteed to be in "OFF" state with  $V_{I(OFF)}$  up to -0.3V.

11. The device is guaranteed to be in "ON" state with  $V_{I(ON)}$  starting from -1.4V.

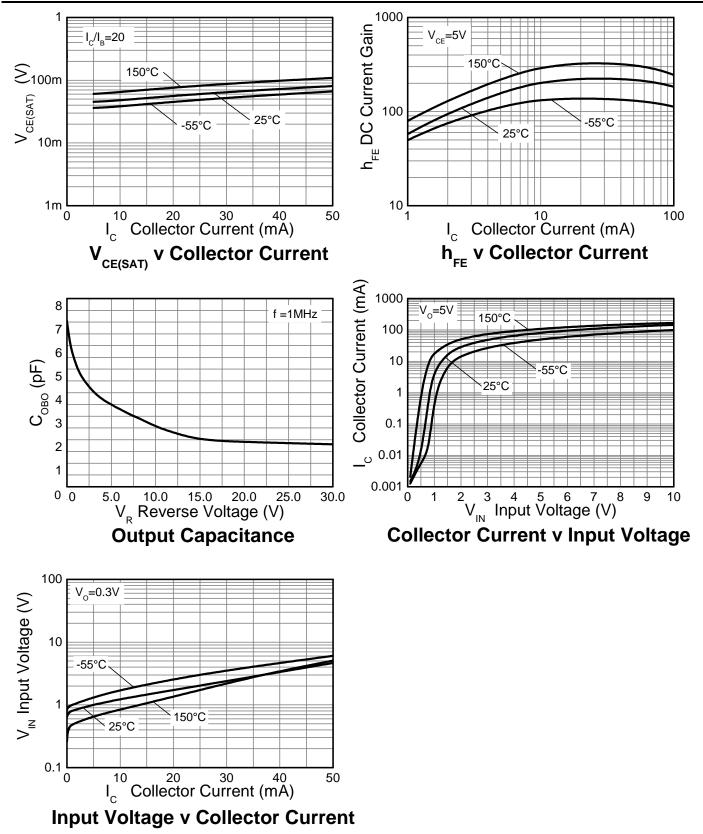


# Typical Electrical Characteristics – NPN Section (@T<sub>A</sub> = +25°C, unless otherwise specified.)





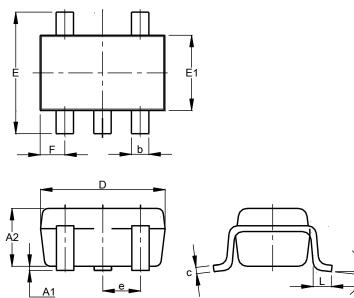
# Typical Electrical Characteristics – PNP Section (@T<sub>A</sub> = +25°C, unless otherwise specified.)





# **Package Outline Dimensions**

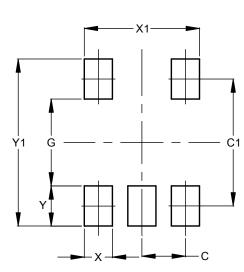
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT353						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	1.00			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All	All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	0.650		
C1	1.900		
G	1.300		
Х	0.420		
X1	1.720		
Ŷ	0.600		
Y1	2.500		

#### SOT353

SOT353



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